### Yoshinori Takao

# List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

104<br/>papers1,002<br/>citations18<br/>h-index24<br/>g-index120<br/>ext. papers1,168<br/>ext. citations1.9<br/>avg, IF4.45<br/>L-index

| #   | Paper   | IF  | Citations |
|-----|---|-----|-----------|
| 104 | Experimental study on the performance characteristics of a miniature microwave discharge cathode. <i>Acta Astronautica</i> , <b>2022</b> , 196, 231-237   | 2.9 |           |
| 103 | Uniform needle-emitter arrays for ionic liquid electrospray thrusters with precise thrust control.<br>Japanese Journal of Applied Physics, 2021, 60, SCCL06   | 1.4 | 0         |
| 102 | Fabrication of nano-capillary emitter arrays for ionic liquid electrospray thrusters. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SCCF07   | 1.4 | O         |
| 101 | Numerical investigation of internal plasma currents in a magnetic nozzle. <i>Physics of Plasmas</i> , <b>2021</b> , 28, 093506  | 2.1 | 5         |
| 100 | Electron loss mechanisms in a miniature microwave discharge water neutralizer. <i>Physics of Plasmas</i> , <b>2020</b> , 27, 063505   | 2.1 | 2         |
| 99  | Mechanism of Highly Efficient Electron Emission from a Graphene/Oxide/Semiconductor Structure. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 2265-2273   | 4   | 5         |
| 98  | Design of High Efficiency Grid System for Water Propellant Miniature Ion Thrusters. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan</i> , <b>2020</b> , 18, 412-416 | 0.3 |           |
| 97  | Increased Thrust-to-Power Ratio of a Stepped-Diameter Helicon Plasma Thruster with Krypton Propellant. <i>Journal of Propulsion and Power</i> , <b>2020</b> , 36, 961-965   | 1.8 | 5         |
| 96  | Commentary: On helicon thrusters: Will they ever fly?. Frontiers in Physics, 2020, 8,   | 3.9 | 2         |
| 95  | Low-power-consumption, high-current-density, and propellantless cathode using graphene-oxide-semiconductor structure array. <i>Acta Astronautica</i> , <b>2020</b> , 174, 48-54   | 2.9 | 5         |
| 94  | Fabrication of a high-density emitter array for electrospray thrusters using field emitter array process. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SEEG04   | 1.4 | 4         |
| 93  | High-performance planar-type electron source based on a graphene-oxide-semiconductor structure. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 213501  | 3.4 | 16        |
| 92  | Assessment of Micropropulsion System Unifying Water Ion Thrusters and Water Resistojet Thrusters. <i>Journal of Spacecraft and Rockets</i> , <b>2019</b> , 56, 1400-1408  | 1.5 | 8         |
| 91  | Effects of negative ions on discharge characteristics of water plasma source for a miniature microwave discharge ion thruster. <i>Physics of Plasmas</i> , <b>2019</b> , 26, 043508                                     | 2.1 | 11        |
| 90  | Computational design of a high-efficiency accelerator grid for a miniature ion thruster by full-aperture ion optics simulations. <i>AIP Advances</i> , <b>2019</b> , 9, 035343  | 1.5 | 1         |
| 89  | Microplasma thruster powered by X-band microwaves. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 083301  | 2.5 | 3         |
| 88  | Low-magnetic-field enhancement of thrust imparted by a stepped-diameter and downstream-gas-injected rf plasma thruster. <i>Plasma Sources Science and Technology</i> , <b>2019</b> , 28, 085014                         | 3.5 | 4         |

## (2016-2019)

| 87 | Electron extraction enhancement via the magnetic field in a miniature microwave discharge neutralizer. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 243302   | 2.5 | 5  |  |
|----|--|-----|----|--|
| 86 | Effects of neutral distribution and external magnetic field on plasma momentum in electrodeless plasma thrusters. <i>Physics of Plasmas</i> , <b>2018</b> , 25, 023507   | 2.1 | 11 |  |
| 85 | Numerical simulation of full-aperture-pair ion optics in a miniature ion thruster. <i>Physics of Plasmas</i> , <b>2018</b> , 25, 013524  | 2.1 | 13 |  |
| 84 | Thrust imparted by a stepped-diameter magnetic nozzle rf plasma thruster. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 034101   | 3.4 | 7  |  |
| 83 | Numerical Investigation of Neutral-Injection Effect on an Electrodeless Plasma Thruster.  Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan,  2018, 16, 105-109   | 0.3 |    |  |
| 82 | Numerical Investigation of Steady and Transient Ion Beam Extraction Mechanisms for Electrospray Thrusters. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan</i> , <b>2018</b> , 16, 110-115             | 0.3 | 3  |  |
| 81 | Investigation of Ion Species in Water Plasma Discharges for Miniature Microwave Discharge Ion Thrusters <b>2018</b> ,  |     | 1  |  |
| 80 | Fabrication of Electrospray Thrusters with a High-Density Emitter Array Utilizing Minimal-Fab System <b>2018</b> ,   |     | 1  |  |
| 79 | Development of a momentum vector measurement instrument in steady-state plasmas. <i>AIP Advances</i> , <b>2018</b> , 8, 105117   | 1.5 | 7  |  |
| 78 | Origin of plasma-induced surface roughening and ripple formation during plasma etching: The crucial role of ion reflection. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 143301  | 2.5 | 4  |  |
| 77 | Ripple formation on Si surfaces during plasma etching in Cl2. AIP Advances, 2018, 8, 055027  | 1.5 | 3  |  |
| 76 | A Preliminary Study on Radiation Shielding Using Martian Magnetic Anomalies. <i>Uchu Seibutsu Kagaku</i> , <b>2018</b> , 32, 1-5   | 1   | 2  |  |
| 75 | Numerical Analysis of a Miniature Microwave-discharge Ion Thruster Using Water as the Propellant. <i>Transactions of the Japan Society for Aeronautical and Space Sciences</i> , <b>2018</b> , 61, 152-159   | 0.8 | 13 |  |
| 74 | Effects of E IB drift on electron transport across the magnetic field in a miniature microwave discharge neutralizer. <i>Physics of Plasmas</i> , <b>2017</b> , 24, 064504   | 2.1 | 14 |  |
| 73 | Surface morphology evolution during plasma etching of silicon: roughening, smoothing and ripple formation. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 414001  | 3   | 11 |  |
| 72 | Microfabricated emitter array for an ionic liquid electrospray thruster. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 06GN18   | 1.4 | 13 |  |
| 71 | Numerical Investigation of Ion Beam Extraction Mechanism for Electrospray Thruster. <i>The Proceedings of Conference of Kanto Branch</i> , <b>2017</b> , 2017.23, 816  | О   |    |  |
| 70 | Investigation of Electron Extraction from a Microwave Discharge Neutralizer for a Miniature Ion Propulsion System. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan</i> , <b>2016</b> , 14, Pb_41-Pb_46 | 0.3 | 7  |  |

| 69 | Optimization of Plasma Production with Impedance Analysis for a Micro RF Ion Thruster.  Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan,  2016, 14, Pb_63-Pb_68                               | 0.3 |    |
|----|--|-----|----|
| 68 | Investigation of Ion Beam Extraction Mechanism for Higher Thrust Density of Ion Thrusters.  Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan, 2016, 14, Pb_57-Pb_62                            | 0.3 | 1  |
| 67 | Evaluation technique for plasma-induced SiOC dielectric damage by capacitance loltage hysteresis monitoring. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 06HB04   | 1.4 | 10 |
| 66 | Electron extraction mechanisms of a micro-ECR neutralizer. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 07LD09   | 1.4 | 9  |
| 65 | Surface smoothing during plasma etching of Si in Cl2. Applied Physics Letters, 2016, 109, 204101   | 3.4 | 5  |
| 64 | Modifications of plasma density profile and thrust by neutral injection in a helicon plasma thruster. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 194101   | 3.4 | 26 |
| 63 | Neutral-depletion-induced axially asymmetric density in a helicon source and imparted thrust. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 074103   | 3.4 | 28 |
| 62 | Silicon nanowire growth on Si and SiO2substrates by rf magnetron sputtering in Ar/H2. <i>Applied Physics Express</i> , <b>2015</b> , 8, 066201   | 2.4 | 2  |
| 61 | Molecular dynamics simulations of Si etching in Cl- and Br-based plasmas: Cl+ and Br+ ion incidence in the presence of Cl and Br neutrals. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 233304                                       | 2.5 | 13 |
| 60 | Numerical validation of axial plasma momentum lost to a lateral wall induced by neutral depletion. <i>Physics of Plasmas</i> , <b>2015</b> , 22, 113509  | 2.1 | 20 |
| 59 | A new aspect of plasma-induced physical damage in three-dimensional scaled structures   Sidewall damage by stochastic straggling and sputtering <b>2014</b> ,  |     | 7  |
| 58 | Random telegraph noise as a new measure of plasma-induced charging damage in MOSFETs <b>2014</b> ,   |     | 1  |
| 57 | Investigation of Plasma Characteristics and Ion Beam Extraction for a Micro RF Ion Thruster.  Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan, 2014, 12, Pb_13-Pb_18                          | 0.3 | 4  |
| 56 | Micro-photoreflectance spectroscopy for microscale monitoring of plasma-induced physical damage on Si substrate. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 03DF01   | 1.4 |    |
| 55 | Effects of straggling of incident ions on plasma-induced damage creation in <b>fi</b> nEtype field-effect transistors. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 03DE02   | 1.4 | 24 |
| 54 | Two modes of surface roughening during plasma etching of silicon: Role of ionized etch products. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 223302   | 2.5 | 15 |
| 53 | Surface roughening and rippling during plasma etching of silicon: Numerical investigations and a comparison with experiments. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 031212 | 1.3 | 17 |
| 52 | A Validation Study of a 3D PIC Model for a Miniature Microwave Discharge Ion Thruster <b>2014</b> ,  |     | 3  |

#### (2011-2014)

| 51 | metallixideBemiconductor field-effect transistors with SiO2and high-kgate dielectrics. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 03DF02   | 1.4               | 1  |  |
|----|--|-------------------|----|--|
| 50 | Molecular dynamics simulations of silicon chloride ion incidence during Si etching in Cl-based plasmas. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 056201  | 1.4               | 18 |  |
| 49 | Three-dimensional particle-in-cell simulation of a miniature plasma source for a microwave discharge ion thruster. <i>Plasma Sources Science and Technology</i> , <b>2014</b> , 23, 064004   | 3.5               | 35 |  |
| 48 | Structural, mechanical, and electrical properties of cubic boron nitride thin films deposited by magnetically enhanced plasma ion plating method. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 03DB                              | 0 <del>2</del> ·4 | 5  |  |
| 47 | Atomistic simulations of plasma process-induced Si substrate damage - Effects of substrate bias-power frequency <b>2013</b> ,  |                   | 7  |  |
| 46 | Plasma Etch Challenges for Nanoscale ULSI Device Fabrication: Modeling and Simulation of Surface Roughening and Rippling during Plasma Etching of Si. <i>Hyomen Kagaku</i> , <b>2013</b> , 34, 528-534   |                   |    |  |
| 45 | Modeling and Simulation of Nanoscale Surface Rippling during Plasma Etching of Si under Oblique Ion Incidence. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 08HC01   | 1.4               | 14 |  |
| 44 | Effect of capacitive coupling in a miniature inductively coupled plasma source. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 093306  | 2.5               | 18 |  |
| 43 | High-k MOSFET performance degradation by plasma process-induced charging damage Impacts on device parameter variation <b>2012</b> ,  |                   | 3  |  |
| 42 | Modeling and Simulation of Nanoscale Surface Rippling during Plasma Etching of Si under Oblique Ion Incidence. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 08HC01   | 1.4               | 6  |  |
| 41 | Particle Simulations of Sheath Dynamics in Low-Pressure Capacitively Coupled Argon Plasma Discharges. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JC02  | 1.4               | 5  |  |
| 40 | Trade-Off Relationship between Si Recess and Defect Density Formed by Plasma-Induced Damage in Planar Metal®xideBemiconductor Field-Effect Transistors and the Optimization Methodology.  Japanese Journal of Applied Physics, 2011, 50, 08KD04    | 1.4               | 2  |  |
| 39 | Comparative Study of Plasma-Charging Damage in High-\$k\$ Dielectric and pl Junction and Their Effects on Off-State Leakage Current of Metall Dxide Bemiconductor Field-Effect Transistors.  Japanese Journal of Applied Physics, 2011, 50, 08KD05 | 1.4               | 1  |  |
| 38 | Molecular Dynamics Analysis of the Formation of Surface Roughness during Si Etching in Chlorine-Based Plasmas. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08KB02   | 1.4               | 3  |  |
| 37 | Advanced Contactless Analysis of Plasma-Induced Damage on Si by Temperature-Controlled Photoreflectance Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08KD03  | 1.4               | 5  |  |
| 36 | Analytic Model of Threshold Voltage Variation Induced by Plasma Charging Damage in High-\$k\$ Metal®xideBemiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 10PG0                                | 2 <sup>1.4</sup>  | 2  |  |
| 35 | Model for Effects of RF Bias Frequency and Waveform on Si Damaged-Layer Formation during Plasma Etching. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JE04   | 1.4               |    |  |
| 34 | PIC-MCC Simulations of Capacitive RF Discharges for Plasma Etching <b>2011</b> ,   |                   | 3  |  |

| 33 | Structural and electrical characterization of HBr/O2 plasma damage to Si substratea). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2011</b> , 29, 041301  | 2.9                | 34 |  |
|----|---|--------------------|----|--|
| 32 | Modeling of plasma-induced damage and its impacts on parameter variations in advanced electronic devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2011</b> , 29, 041303                                  | 2.9                | 17 |  |
| 31 | Three-Dimensional Atomic-Scale Cellular Model and Feature Profile Evolution during Si Etching in Chlorine-Based Plasmas: Analysis of Profile Anomalies and Surface Roughness. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JE06 | 1.4                | 3  |  |
| 30 | A new prediction model for effects of plasma-induced damage on parameter variations in advanced LSIs <b>2011</b> ,  |                    | 3  |  |
| 29 | Microwave-excited microplasma thruster with helium and hydrogen propellants. <i>Physics of Plasmas</i> , <b>2011</b> , 18, 063505   | 2.1                | 18 |  |
| 28 | Particle Simulations of Sheath Dynamics in Low-Pressure Capacitively Coupled Argon Plasma Discharges. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JC02   | 1.4                | 6  |  |
| 27 | Model for Effects of RF Bias Frequency and Waveform on Si Damaged-Layer Formation during Plasma Etching. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JE04  | 1.4                | 6  |  |
| 26 | Three-Dimensional Atomic-Scale Cellular Model and Feature Profile Evolution during Si Etching in Chlorine-Based Plasmas: Analysis of Profile Anomalies and Surface Roughness. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08JE06 | 1.4                | 3  |  |
| 25 | Molecular Dynamics Analysis of the Formation of Surface Roughness during Si Etching in Chlorine-Based Plasmas. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08KB02  | 1.4                | 2  |  |
| 24 | Trade-Off Relationship between Si Recess and Defect Density Formed by Plasma-Induced Damage in Planar Metal Dxide Bemiconductor Field-Effect Transistors and the Optimization Methodology.  Japanese Journal of Applied Physics, 2011, 50, 08KD04   | 1.4                | 5  |  |
| 23 | Analytic Model of Threshold Voltage Variation Induced by Plasma Charging Damage in High-kMetalDxideBemiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 10PG02                                     | 1.4                | 5  |  |
| 22 | Advanced Contactless Analysis of Plasma-Induced Damage on Si by Temperature-Controlled Photoreflectance Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 08KD03   | 1.4                | 4  |  |
| 21 | Two-dimensional particle-in-cell Monte Carlo simulation of a miniature inductively coupled plasma source. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 093309   | 2.5                | 25 |  |
| 20 | Optical and Electrical Characterization of Hydrogen-Plasma-Damaged Silicon Surface Structures and Its Impact on In-line Monitoring. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 08JD02   | 1.4                | 46 |  |
| 19 | Threshold Voltage Instability Induced by Plasma Process Damage in Advanced Metal Dxide Bemiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 08JC  | :0 <del>2</del> ·4 | 9  |  |
| 18 | Atomic-Scale Cellular Model and Profile Simulation of Si Etching: Analysis of Profile Anomalies and Microscopic Uniformity. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 08JE01   | 1.4                | 17 |  |
| 17 | Model for Bias Frequency Effects on Plasma-Damaged Layer Formation in Si Substrates. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 056203  | 1.4                | 24 |  |
| 16 | Comprehensive Modeling of Threshold Voltage Variability Induced by Plasma Damage in Advanced Metal®xideBemiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 04D                                   | 41 <del>8</del> 4  | 8  |  |

#### LIST OF PUBLICATIONS

| 15 | Modeling the effects of plasma-induced physical damage on subthreshold leakage current in scaled MOSFETs <b>2010</b> ,   |               | 2          |
|----|--|---------------|------------|
| 14 | Atomic-scale cellular model and profile simulation of Si etching: Formation of surface roughness and residue. <i>Thin Solid Films</i> , <b>2010</b> , 518, 3475-3480                                   | 2.2           | <b>2</b> 0 |
| 13 | Modeling of ion-bombardment damage on Si surfaces for in-line analysis. <i>Thin Solid Films</i> , <b>2010</b> , 518, 3481-3486   | 2.2           | 41         |
| 12 | Numerical and experimental study of microwave-excited microplasma and micronozzle flow for a microplasma thruster. <i>Physics of Plasmas</i> , <b>2009</b> , 16, 083505                                | 2.1           | 18         |
| 11 | Plasma-Induced Defect-Site Generation in Si Substrate and Its Impact on Performance Degradation in Scaled MOSFETs. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 1275-1277                   | 4.4           | 36         |
| 10 | Plasma chemical behaviour of reactants and reaction products during inductively coupled CF4plasma etching of SiO2. <i>Plasma Sources Science and Technology</i> , <b>2009</b> , 18, 045027             | 3.5           | 25         |
| 9  | Numerical Simulation of a Microwave-Excited Microplasma Thruster. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Space Technology Japan</i> , <b>2009</b> , 7, Pb_135-Pb_140 |               |            |
| 8  | Microplasma thruster for ultra-small satellites: Plasma chemical and aerodynamical aspects. <i>Pure and Applied Chemistry</i> , <b>2008</b> , 80, 2013-2023  | 2.1           | 20         |
| 7  | Microwave-excited microplasma thruster: a numerical and experimental study of the plasma generation and micronozzle flow. <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 194005         | 3             | 13         |
| 6  | A miniature electrothermal thruster using microwave-excited microplasmas: Thrust measurement and its comparison with numerical analysis. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 123307 | 2.5           | 27         |
| 5  | Development of small microwave discharge ion thruster. <i>Thin Solid Films</i> , <b>2006</b> , 506-507, 605-608  | 2.2           | 5          |
| 4  | Plasma Diagnostics and Thrust Performance Analysis of a Microwave-Excited Microplasma Thruster.<br>Japanese Journal of Applied Physics, <b>2006</b> , 45, 8235-8240                                    | 1.4           | 20         |
| 3  | A miniature electrothermal thruster using microwave-excited plasmas: a numerical design consideration. <i>Plasma Sources Science and Technology</i> , <b>2006</b> , 15, 211-227                        | 3.5           | 31         |
| 2  | Microwave-sustained miniature plasmas for an ultra small thruster. <i>Thin Solid Films</i> , <b>2006</b> , 506-507, 592  | 2-5 <u>96</u> | 8          |

Development of Microplasma Thruster. *Journal of High Temperature Society*, **2005**, 31, 283-290